

## SILICON PLANAR EPITAXIAL TRANSISTORS

General purpose n-p-n transistors in TO-92 packages. The complementary types are MPS6517 to MPS6519.

### QUICK REFERENCE DATA

|  |                  |      | MPS6513 | 6514 | 6515   |
|--|------------------|------|---------|------|--------|
| Collector-emitter voltage  | V <sub>CEO</sub> | max. | 30      | 25   | 25 V   |
| Collector current (d.c.)   | I <sub>C</sub>   | max. | 100     | 100  | 100 mA |
| D.C. current gain<br>$I_C = 100 \text{ mA}; V_{CE} = 10 \text{ V}$ | h <sub>FE</sub>  | >    | 60      | 90   | 150    |
| Total power dissipation<br>up to T <sub>amb</sub> = 25 °C          | P <sub>tot</sub> | max. | 625     | mW   |        |

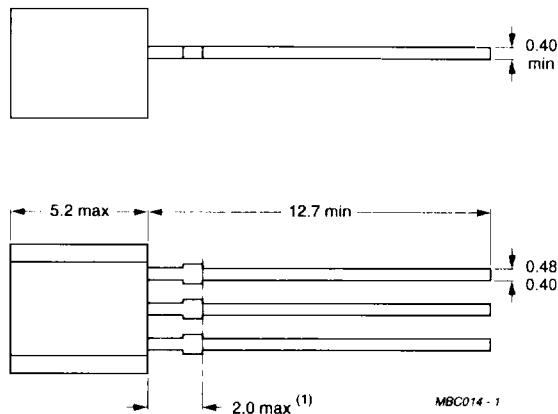
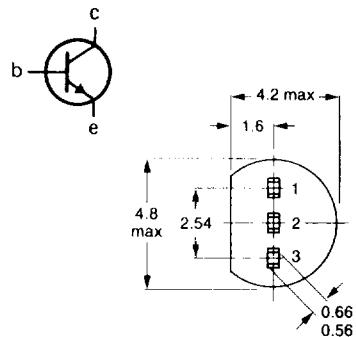
### MECHANICAL DATA

Dimensions in mm

Fig. 1 TO-92.

Pinning:

- 1 = collector
- 2 = base
- 3 = emitter



Note (1) Terminal dimensions within this zone are uncontrolled to allow for flow of plastic and terminal irregularities.

## RATINGS

Limiting values in accordance with the Absolute Maximum System (IEC 134)

|   |           |      | <b>MPS6513</b> | <b>6514</b> | <b>6515</b>      |
|---|-----------|------|----------------|-------------|------------------|
| Collector-emitter voltage                                     | $V_{CEO}$ | max. | 30             | 25          | 25 V             |
| Collector-base voltage  | $V_{CBO}$ | max. |                | 40          | V                |
| Emitter-base voltage  | $V_{EBO}$ | max. |                | 4,0         | V                |
| Collector current (d.c.)                                      | $I_C$     | max. |                | 100         | mA               |
| Total power dissipation<br>up to $T_{amb} = 25^\circ\text{C}$ | $P_{tot}$ | max. |                | 625         | mW               |
| Storage temperature range                                     | $T_{stg}$ |      |                | -65 to +150 | $^\circ\text{C}$ |
| Junction temperature  | $T_j$     | max. |                | 150         | $^\circ\text{C}$ |

## THERMAL RESISTANCE

|                                      |              |   |     |     |
|--------------------------------------|--------------|---|-----|-----|
| From junction to ambient in free air | $R_{th j-a}$ | = | 200 | K/W |
|--------------------------------------|--------------|---|-----|-----|

## CHARACTERISTICS

$T_j = 25^\circ\text{C}$  unless otherwise specified

|   |               |   | <b>MPS6513</b>  | <b>6514</b>      | <b>6515</b>      |
|---|---------------|---|-----------------|------------------|------------------|
| Collector-emitter breakdown voltage<br>$I_C = 0,5 \text{ mA}; I_B = 0$            | $V_{(BR)CEO}$ | > | 30              | 25               | 25 V             |
| Emitter-base breakdown voltage<br>$I_E = 10 \mu\text{A}; I_C = 0$                 | $V_{(BR)EBO}$ | > | 4,0             | 4,0              | 4,0 V            |
| Collector cut-off current<br>$V_{CB} = 30 \text{ V}; I_E = 0$                     | $I_{CBO}$     | < | 50              | 50               | 50 nA            |
| D.C. current gain<br>$I_C = 2 \text{ mA}; V_{CE} = 10 \text{ V}$                  | $h_{FE}$      | = | 90<br>to<br>180 | 150<br>to<br>300 | 250<br>to<br>500 |
| $I_C = 100 \text{ mA}; V_{CE} = 10 \text{ V}$                                     | $h_{FE}$      | > | 60              | 90               | 150              |
| Collector-emitter saturation voltage<br>$I_C = 50 \text{ mA}; I_B = 5 \text{ mA}$ | $V_{CEsat}$   | < |                 | 0,5              | V                |
| Output capacitance<br>$V_{CB} = 10 \text{ V}; I_E = 0; f = 100 \text{ kHz}$       | $C_C$         | < |                 | 3,5              | pF               |